

VERSION WITH MARKINGS TO SHOW CHANGES MADE

In the Drawings:

FIGs. 11, 12A, 12B, 12C, 13A, and 13B have been amended as shown on the drawing copies marked in red and attached to the Request for Approval of Drawing Changes submitted herewith.

In the Claims:

Claims 9, 10, and 20 have been amended as follows:

9. (Amended) A process of production of a semiconductor apparatus as set forth in claim 7, in said third step, the surfaces of the bumps are chemically activated in parallel to the cleaning of the surfaces of the bumps.

10. (Amended) A process of production of the semiconductor apparatus as set forth in claim 7, wherein, in said third step, any [said] resin film components deposited on said bumps are removed.

20. (Amended) A process of production of a semiconductor apparatus as set forth in claim 19, wherein said solder bumps have a melting point higher than a melting point of said solder layers [are high melting point solder] and said solder layers are comprised of a eutectic solder.